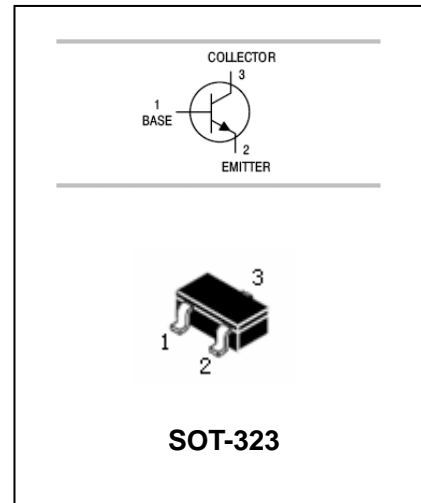


## NPN Silicon Epitaxial Planar Transistor

## 2PD601AW

### FEATURES

- Collector Current.( $I_C=100\text{mA}$ )
- Excellent  $H_{FE}$  Linearity.
- Power dissipation.( $P_C=200\text{mW}$ )



### APPLICATIONS

- General purpose application.

### ORDERING INFORMATION

| Type No. | Marking  | Package Code |
|----------|----------|--------------|
| 2PD601AW | 6D/6E/6F | SOT-323      |

### MAXIMUM RATING @ $T_a=25^\circ\text{C}$ unless otherwise specified

| Symbol         | Parameter                        | Value   | Units            |
|----------------|----------------------------------|---------|------------------|
| $V_{CBO}$      | Collector-Base Voltage           | 60      | V                |
| $V_{CEO}$      | Collector-Emitter Voltage        | 50      | V                |
| $V_{EBO}$      | Emitter-Base Voltage             | 6       | V                |
| $I_C$          | Collector Current -Continuous    | 100     | mA               |
| $P_C$          | Collector Dissipation            | 200     | mW               |
| $T_j, T_{stg}$ | Junction and Storage Temperature | -55~150 | $^\circ\text{C}$ |

**NPN Silicon Epitaxial Planar Transistor****2PD601AW****ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified**

| Parameter                            | Symbol        | Test conditions                              | MIN | TYP | MAX  | UNIT    |
|--------------------------------------|---------------|--|-----|-----|------|---------|
| Collector-base breakdown voltage     | $V_{(BR)CBO}$ | $I_C=100\mu A, I_E=0$                        | 60  |     |      | V       |
| Collector-emitter breakdown voltage  | $V_{(BR)CEO}$ | $I_C=1mA, I_B=0$                             | 50  |     |      | V       |
| Emitter-base breakdown voltage       | $V_{(BR)EBO}$ | $I_E=100\mu A, I_C=0$                        | 6   |     |      | V       |
| Collector cut-off current            | $I_{CBO}$     | $V_{CB}=60V, I_E=0$                          |     |     | 0.01 | $\mu A$ |
| Emitter cut-off current              | $I_{EBO}$     | $V_{EB}=5V, I_C=0$                           |     |     | 0.01 | $\mu A$ |
| DC current gain                      | $h_{FE}$      | $V_{CE}=10V, I_C=2mA$<br>2PD601AQW           | 160 |     | 260  |         |
|                                      |               | 2PD601ARW                                    | 210 |     | 340  |         |
|                                      |               | 2PD601ASW                                    | 290 |     | 460  |         |
|                                      |               | $V_{CE}=2V, I_C=100mA$                       | 90  |     |      |         |
| Collector-emitter saturation voltage | $V_{CE(sat)}$ | $I_C=100mA, I_B=10mA$                        |     |     | 0.5  | V       |
| Transition frequency                 | $f_T$         | $V_{CE}=6V, I_C=2mA$<br>$f=100MHz$ 2PD601AQW | 100 |     |      | MHz     |
|                                      |               | 2PD601ARW                                    | 120 |     |      |         |
|                                      |               | 2PD601ASW                                    | 140 |     |      |         |

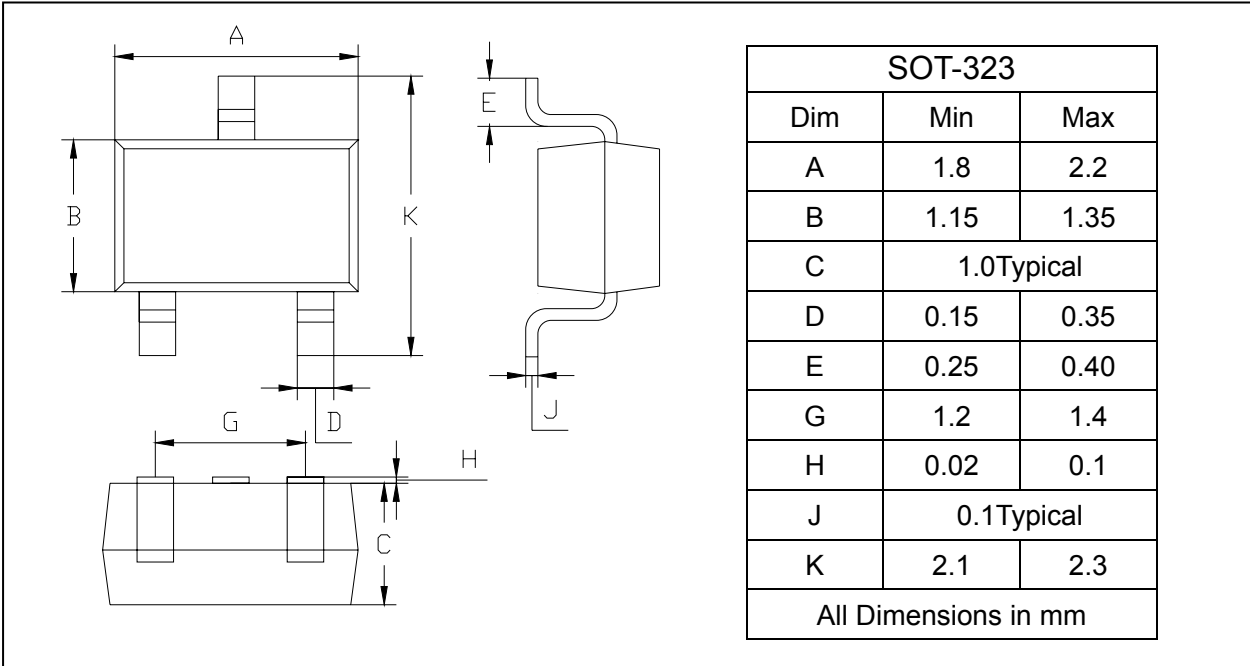
## NPN Silicon Epitaxial Planar Transistor

## 2PD601AW

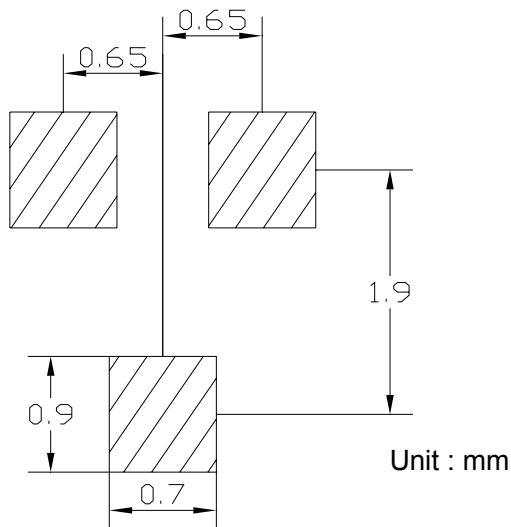
### PACKAGE OUTLINE

Plastic surface mounted package

SOT-323



### SOLDERING FOOTPRINT



### PACKAGE INFORMATION

| Device   | Package | Shipping       |
|----------|---------|----------------|
| 2PD601AW | SOT-323 | 3000/Tape&Reel |

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